

Silicon NPN Power Transistors

2SC1448

DESCRIPTION

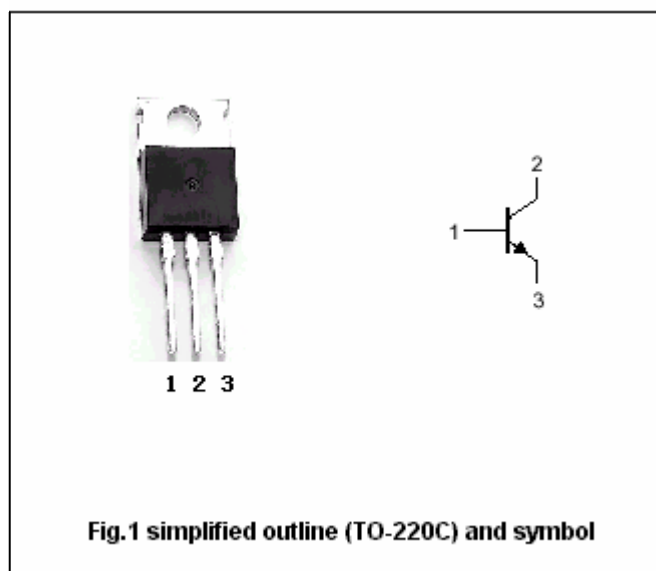
- With TO-220 package
- High collector-emitter breakdown voltage
: $V_{CEO}=150V(\text{min})$

APPLICATIONS

- Power amplifier applications
- Vertical output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	150	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
I_B	Base current		0.5	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	1.5	W
		$T_C=25^\circ\text{C}$	25	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =30mA; I _B =0	150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =0.5A; I _B =50mA			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =150V; I _E =0			20	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			20	μA
h _{FE}	DC current gain	I _C =0.5A; V _{CE} =10V	40		140	
f _T	Transition frequency	I _C =0.5A; V _{CE} =10V		5		MHz

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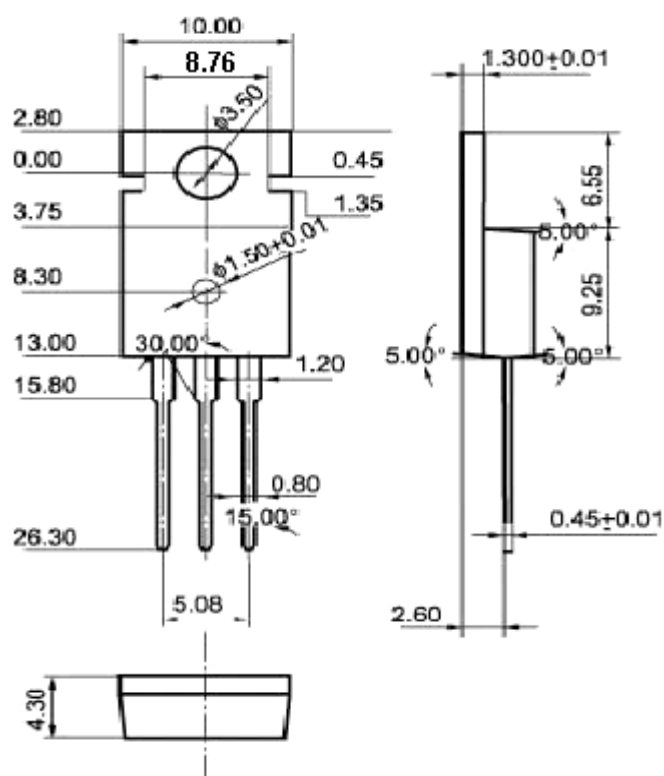


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)